

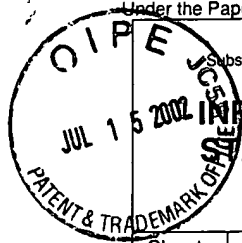
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DATE FILED: July 12, 2002

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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| Applicati n Number | 09/498,303 |
| Filing Date | February 4, 2000 |
| First Named Invent r | Han |
| Group Art Unit | 1763 |
| Examiner Name | T. Dang |
| Attorney Docket Number | MIT7941 |

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| Sheet | 1 | of | 5 |
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U.S. PATENT DOCUMENTS

| Examiner Initials* | Cite No. ¹ | U.S. Patent Document | | Name of Patentee or Applicant Of Cited Document | Date of Publication of Cited Document MM-DD-YYYY | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
|-----------------------|--------------------------|----------------------|--------------------------------------|--|--|--|
| | | Number | Kind Code ² (if known) | | | |
| JD | A1 | 4,127,437 | | Bersin et al. | 11-28-1978 | |
| | B1 | 4,605,479 | | Faith, Jr. | 08-12-1986 | |
| | C1 | 4,806,171 | | Whitlock et al. | 02-21-1989 | |
| | D1 | 4,900,395 | | Syversen et al. | 02-13-1990 | |
| | E1 | 4,904,338 | | Kozicki | 02-27-1990 | |
| | F1 | 4,932,168 | | Tada et al. | 06-12-1990 | |
| | G1 | 5,025,597 | | Tada et al. | 06-25-1991 | |
| | H1 | 5,062,898 | | McDermott et al. | 11-05-1991 | |
| | I1 | 5,073,232 | | Ohmi et al. | 12-17-1991 | |
| | J1 | 5,078,832 | | Tanaka | 01-07-1992 | |
| | K1 | 5,089,084 | | Chhabra et al. | 02-18-1992 | |
| | L1 | 5,089,441 | | Moslehi | 02-18-1992 | |
| | M1 | 5,100,495 | | Ohmi et al. | 03-31-1992 | |
| | N1 | 5,112,437 | | Watanabe et al. | 05-12-1992 | |
| | O1 | 5,129,198 | | Kanno et al. | 07-14-1992 | |
| | P1 | 5,147,466 | | Ohmori et al. | 09-15-1992 | |
| | Q1 | 5,167,761 | | Westendorp et al. | 12-01-1992 | |
| | R1 | 5,173,152 | | Tanaka | 12-22-1992 | |
| | S1 | 5,174,855 | | Tanaka | 12-29-1992 | |
| | T1 | 5,209,028 | | McDermott et al. | 05-11-1993 | |
| | U1 | 5,238,500 | | Bergman | 08-24-1993 | |

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FOREIGN PATENT DOCUMENTS

| Examiner Initials* | Cite No. ¹ | Foreign Patent Document | | | Name of Patentee or Applicant Of Cited Document | Date of Publication of Cited Document MM-DD-YYYY | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T ⁶ |
|-----------------------|--------------------------|-------------------------|---------------------|--------------------------------------|---|--|--|----------------|
| | | Office ³ | Number ⁴ | Kind Code ⁵ (if known) | | | | |
| JD | V1 | WO | 94 27315 | | IMEC Inter Uni Micro Electro.; Adv. Semiconductor Mat. | 11-24-1994 | | |
| | W1 | EP | 0 732 733 | | Nippon Electric; ASM Japan | 09-18-1996 | | |
| | X1 | EP | 0 602 633 | | Texas Instruments | 06-22-1994 | | |
| | Y1 | EP | 0 288 263 | | BOC Group Inc. | 10-26-1988 | | |
| | Z1 | WO | 92 22084 | | Advantage Prod Tech | 12-10-1992 | | |
| | AA1 | JP | 08 316189 | | Hitachi Ltd | 11-29-1996 | | x(Abst). |
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| | | Examiner Name | T. Dang |
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|-----------------------|-----------------------|----------------------|-----------------------------------|---|--|---|
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| | | Number | Kind Code ² (if known) | | | |
| TD | A2 | 5,244,535 | | Ohtsuka et al. | 09-14-1993 | |
| | B2 | 5,268,069 | | Chapple-Sokol et al. | 12-07-1993 | |
| | C2 | 5,294,261 | | McDermott et al. | 03-15-1994 | |
| | D2 | 5,294,568 | | McNeilly et al. | 03-15-1994 | |
| | E2 | 5,315,793 | | Peterson et al. | 05-31-1994 | |
| | F2 | 5,336,356 | | Ban et al. | 08-09-1994 | |
| | G2 | 5,348,619 | | Bohannon et al. | 09-20-1994 | |
| | H2 | 5,357,991 | | Bergman et al. | 10-25-1994 | |
| | I2 | 5,372,652 | | Srikrishnan et al. | 12-13-1994 | |
| | J2 | 5,377,911 | | Bauer et al. | 01-03-1995 | |
| | K2 | 5,378,312 | | Gifford et al. | 01-03-1995 | |
| | L2 | 5,403,434 | | Moslehi | 04-04-1995 | |
| | M2 | 5,425,845 | | Wong | 06-20-1995 | |
| | N2 | 5,439,553 | | Grant et al. | 08-08-1995 | |
| | O2 | 5,456,758 | | Menon | 10-10-1995 | |
| | P2 | 5,512,106 | | Tamai et al. | 04-30-1996 | |
| | Q2 | 5,567,332 | | Mehta | 10-22-1996 | |
| | R2 | 5,580,421 | | Hiatt et al. | 12-03-1996 | |
| | S2 | 5,584,963 | | Takahashi | 12-17-1996 | |
| | T2 | 5,589,422 | | Bhat | 12-31-1996 | |
| | U2 | 5,635,102 | | Mehta | 06-03-1997 | |

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| FOREIGN PATENT DOCUMENTS | | | | | | | | |
|--------------------------|--------------------------|-------------------------|---------------------|--------------------------------------|---|---|---|----------------|
| Examiner Initials* | Cite No. ¹ | Foreign Patent Document | | | Name of Patentee or Applicant Of Cited Document | Date of Publication of Cited Document MM-DD-YYY | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T ⁶ |
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| Sheet | 4 | of | 5 | Application Number | 09/498,303 |
| | | | | Filing Date | February 4, 2000 |
| | | | | First Named Inventor | Han |
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

| Examiner Initials* | Cite No. ¹ | Included name of the author (in CAPITAL LETTERS). Title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published | T ² |
|--------------------|-----------------------|---|----------------|
| TD | A4 | PETERSON et al., "Contamination Removal by CO ₂ Jet Spray," SPIE Vol. 1329, <i>Optical System Contamination: Effects, Measurement, Control II</i> , pp. 72-85, 1990. | |
| | B4 | LAYDEN et al., "High velocity carbon dioxide snow for cleaning vacuum system surfaces," <i>J. Vac. Sci. Technol. A</i> , Vol. 8, No. 5, pp. 3881-3883, Sep/Oct 1990. | |
| | C4 | IZUMI et al., "A New Cleaning Method by Using Anhydrous HF/CH ₃ OH Vapor System," <i>Japanese Journal of Applied Physics</i> , Int. Conf. On Solid State Devices and Materials, pp. 135-137, August 1991. | |
| | D4 | WONG et al., "Characterization of Wafer Cleaning and Oxide Etching Using Vapor-Phase Hydrogen Fluoride," <i>J. Electrochem. Soc.</i> , Vol. 138, No. 6, pp. 1799-1802, June 1991. | |
| | E4 | SYVERSON et al., "The Removal of Reactive Ion Etch Residues," Technical Report WC/DC/WS/R, TR 386, FSI International, Chaska, MN, May 10, 1993. | |
| | F4 | SYVERSON et al., "Post Metal Etch Residue Removal Using Vapor Phase Processing Tech.," Technical Report WC/DC/WS/R, TR 392, FSI International, Chaska, MN, May 24, 1993. | |
| | G4 | GAY et al., "Vapor Phase cleaning of Submicron Inter-Metal Vias," Technical Report DC/DE, TR 397, FSI International, Chaska, MN, November, 1993. | |
| | H4 | BOHANNON et al., "Polysilicon Emitter Vapor Clean Characterization on an EXCALIBUR MVP," Technical Report DCSE, TR 393, FSI International, Chaska, MN, November 10, 1993. | |
| | I4 | BOHANNON et al., "Titanium Salicide Vapor Clean Development on an EXCALIBUR MVP," Technical Report DCSE, TR 394, FSI International, Chaska, MN, November 10, 1993. | |
| | J4 | WERKHOVEN et al., "Cluster-Tool Integrated HF Vapor Etching For Native Oxide Free Processing," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 315, pp. 211-217, 1993. | |
| | K4 | WATANABE et al., "Influence of Water Adsorption/Desorption Processes on the Selectivity of Vapor HF Etching," <i>J. Electrochem. Soc.</i> , Vol. 142, No. 4, pp. 1332-1340, April 1995. | |
| | L4 | TONG et al., "The Removal of Polymeric/Silicate Residues and Reduction of Contact Resistance for Inter-metal Via Holes by Vapor Phase HF Cleaning," Surface Conditioning Systems Technical Report, Document No. 1024-TRS-1196, FSI International, Chaska, MN, October 1996. | |
| | M4 | ALLGAIR et al., "Nanoscale patterning of silicon dioxide thin films by catalyzed HF vapor etching," <i>Nanotechnology</i> , Vol. 7, pp. 351-355, 1996. | |
| | N4 | LEE et al., "Dry Release for Surface Micromachining with HF Vapor-Phase Etching," <i>Journal of Microelectromechanical Systems</i> , Vol. 6, No. 3, pp. 226-232, September 1997. | |

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







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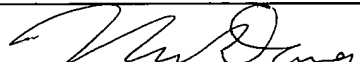
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| OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS | | | |
|--|-----------------------|---|----------------|
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|             | A5 | SAITO et al., "X-ray Photoelectron Study on the Adsorption of Anhydrous Hydrogen Fluoride onto Silicon Native Oxide," <i>Jpn. J. Appl. Phys.</i> , Vol. 36, Part 2, No. 11A, pp. L1466-L1469, November 1997. | |
| | B5 | HABUKA et al., "In situ cleaning method for silicon surface using hydrogen fluoride gas and hydrogen chloride gas in a hydrogen ambient," <i>Journal of Crystal Growth</i> , Vol. 186, pp. 104-112, 1998. | |
| | C5 | NAKAZAWA et al., "Selective Etching of Silicon Native Oxide with Remote-Plasma-Excited Anhydrous Hydrogen Fluoride," <i>Jpn. J. Appl. Phys.</i> , Vol. 37, Part 2, No. 5A, pp. L537-538, May 1998. | |
| | D5 | CHANG et al., "Anhydrous HF etch reduces processing steps for DRAM capacitors," <i>Solid State Technology</i> , pp. 71-76, May 1998. | |
| | E5 | SHERMAN et al., "The removal of hydrocarbons and silicone grease stains from silicon wafers," <i>J. Vac., Sci. Technol. B</i> , Vol. 8, No. 3, pp. 563-567, May/June 1990. | |
| | F5 | PHILIPOSSIAN, "The Activity of HF/H ₂ O Treated Silicon Surfaces in Ambient Air Before and After Gate Oxidation," <i>Proc., Second Int. Symp. On Cleaning Technology in Semiconductor Device Manufacturing</i> , pp. 234-250, Oct. 1992. | |
| | G5 | NAKANISHI et al., "Precise Control of SiO ₂ Etching Characteristics Using Mono-Layer Adsorption of Hf/H ₂ O Vapor," <i>Int. Conf. On Solid State Devices & Materials</i> , Extended Abstracts, C-1-4, pp. 255-257, August 1995. | |
| | H5 | PATENT ABSTRACTS OF JAPAN, Vol. 1997, No. 03, & JP 08316189A, Hitachi Ltd., March 1997. | |
| | I5 | HAN et al., "Characterization of Silicon Oxide Etching and Cleaning in HF Vapor Process," <i>Meeting Abstracts, Fifth Int. Symp. On Cleaning Technology in Semiconductor Device Manufacturing</i> , ECS, Paris, France, August 1997. | |
| | J5 | HAN et al., "Characterization of Silicon Oxide Etching and Cleaning in HF Vapor Process," <i>Proceedings, Cleaning Technology in Semiconductor Device Manufacturing V</i> , Novak et al., Editors, February 27, 1998. | |
| | K5 | HAN et al., "Etching and Cleaning of Silicon Wafers using HF Vapor Process in the Non-condensed Etching Regime," Abstract, <i>American Vacuum Society National Meeting</i> , Baltimore, MD, November 1998. | |
| | L5 | HAN et al., "Characterization of Silicon Oxide Etching in HF Vapor Process," Abstract, <i>American Vacuum Society National Meeting</i> , San Jose, CA, November 1997. | |
| | M5 | HAN, "HF Vapor Etching and Cleaning of Silicon Wafer Surfaces," Ph.D. Thesis, Massachusetts Institute of Technology, Cambridge, MA, July 1999. | |
| | N5 | KWON, "Post Oxide Etching Cleaning Process Using Integrated Ashing and HF Vapor Process," Masters Thesis, Massachusetts Institute of Technology, Cambridge, MA, May 1999. | |

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| Examiner Signature |  | Date Considered | 10/2/02 |
|--------------------|---|-----------------|---------|

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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